



JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

TO-92K Plastic-Encapsulate Thyristors

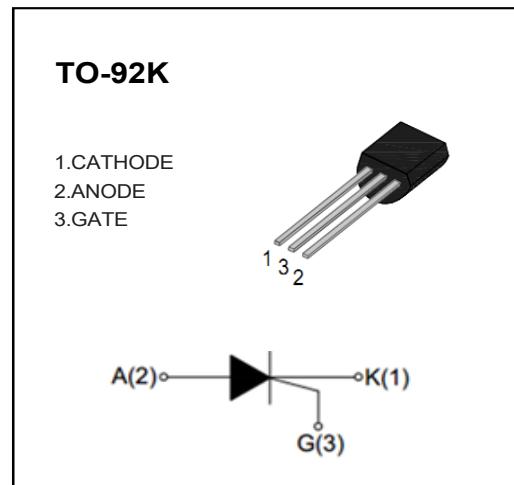
CS008G Sensitive Gate SCRs

MAIN CHARACTERISTICS

$I_{T(AV)}$	0.5A
V_{DRM}/V_{RRM}	600V
I_{GT}	200μA

FEATURES

- PNPN 4-layer Structure SCRs
- Mesa Glass Passivated Technology
- Multi Layers Metal Electrodes
- Sensitive gate trigger



APPLICATIONS

- Pulse Igniter
- Leakage Protector
- Logic Circuit Driver

MARKING

CS008G
XXX XXX

CS008G:Part Number

XXX:Internal Code

ABSOLUTE RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test condition	Value	Unit
V_{DRM}/ V_{RRM}	Repetitive peak off-state voltage	$T_j=25^\circ\text{C}$	600	V
$I_{T(AV)}$	Average on-state current	TO-92K($T_c \leq 63^\circ\text{C}$)	0.5	A
$I_{T(RMS)}$	RMS on-state current	TO-92K($T_c \leq 63^\circ\text{C}$),Fig. 1,2	0.8	A
I_{TSM}	Non repetitive surge peak on-state current	Full sine wave , $T_j(\text{init})=25^\circ\text{C}$, $tp=20\text{ms}$; Fig. 3,5	8	A
I^2t	I^2t value	$tp=10\text{ms}$	0.32	A^2s
dI_t/dt	Critical rate of rise of on-state current	$I_G=2*I_{GT}$, $tr \leq 10\text{ns}$, $F=120\text{Hz}$, $T_j=110^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current	$tp=20\mu\text{s}$, $T_j=110^\circ\text{C}$	0.2	A
$P_{G(AV)}$	Average gate power	$T_j=110^\circ\text{C}$	0.1	W
T_{STG}	Storage temperature		-40~+150	$^\circ\text{C}$
T_j	Operating junction temperature		-40~+110	

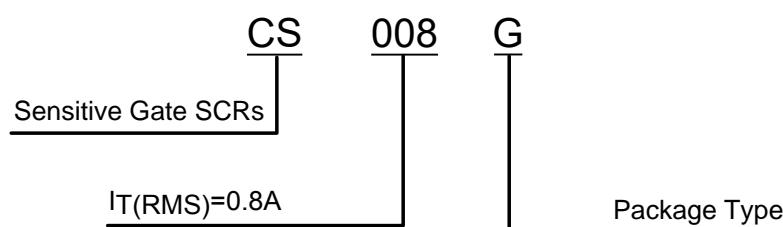
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test condition	Value			Unit
			Min	Nom	Max	
I_{GT}	Gate trigger current	$V_D=12\text{V}$, $I_T = 10\text{mA}$, $T_j=25^\circ\text{C}$, Fig. 6	10	-	200	μA
V_{GT}	Gate trigger voltage	$V_D=12\text{V}$, $I_T = 10\text{mA}$, $T_j=25^\circ\text{C}$	-	-	0.8	V
V_{GD}	Non-triggering gate voltage	$V_D=V_{DRM}$, $T_j=125^\circ\text{C}$	0.2	-	-	V
I_H	Holding current	$V_D=12\text{V}$, $I_G=0.5\text{mA}$, $R_{GK}=1\text{k}\Omega$, $T_j=25^\circ\text{C}$, Fig. 6	-	-	3	mA
I_L	Latching current	$V_D=V_{DRM}/V_{RRM}, T_j=110^\circ\text{C}$	-	-	4	mA
dV_D/dt	Critical rate of rise of off-state	$V_D=67\%V_{DRM}$, $R_{GK}=1\text{k}\Omega, T_j=110^\circ\text{C}$	10	-	-	$\text{V}/\mu\text{s}$
V_{TM}	On-state Voltage	$I_{TM}=1.2\text{A}$, , Fig. 4	-	-	1.5	V
I_{DRM} / I_{RRM}	Repetitive peak off-state current	$V_D=V_{DRM}/V_{RRM}, T_j=25^\circ\text{C}$	-	-	5	μA
		$V_D=V_{DRM}/V_{RRM}, T_j=110^\circ\text{C}$	-	-	100	μA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th} (j-c)$	Junction to case (AC)	75	$^\circ\text{C}/\text{W}$
$R_{th} (j-a)$	Junction to ambient	150	$^\circ\text{C}/\text{W}$

PART NUMBER



CHARACTERISTICS CURVES

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

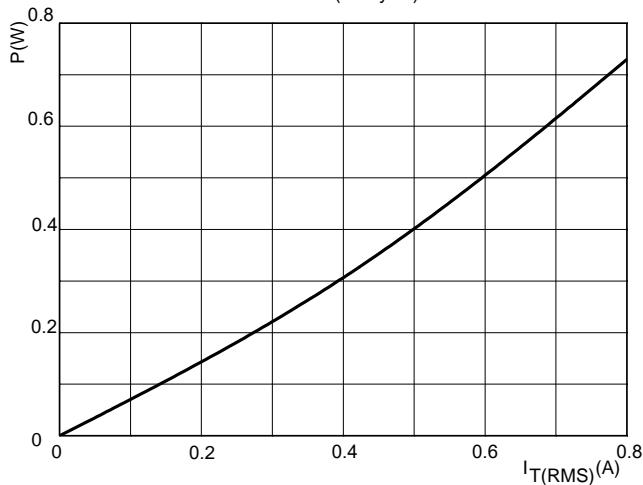


FIG.2: RMS on-state current versus case temperature (full cycle)

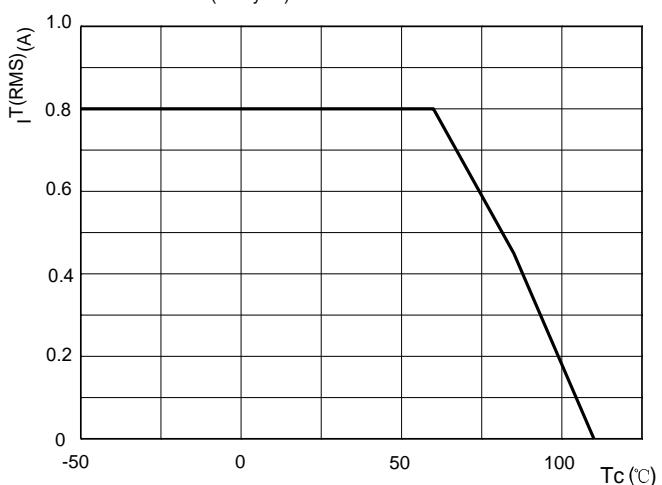


FIG.3: Surge peak on-state current versus number of cycles

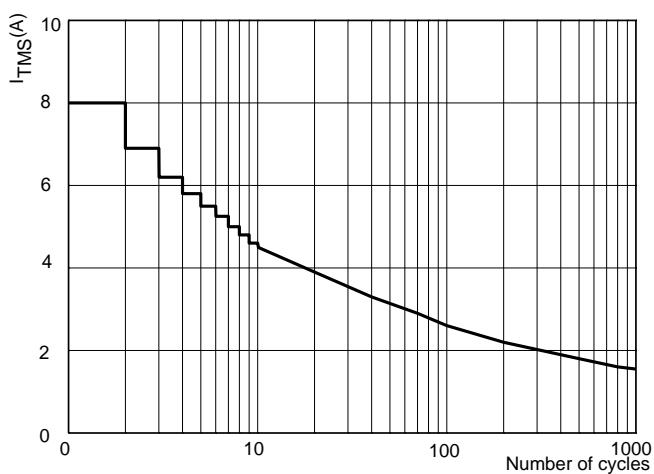


FIG.4: On-state characteristics (maximum values)

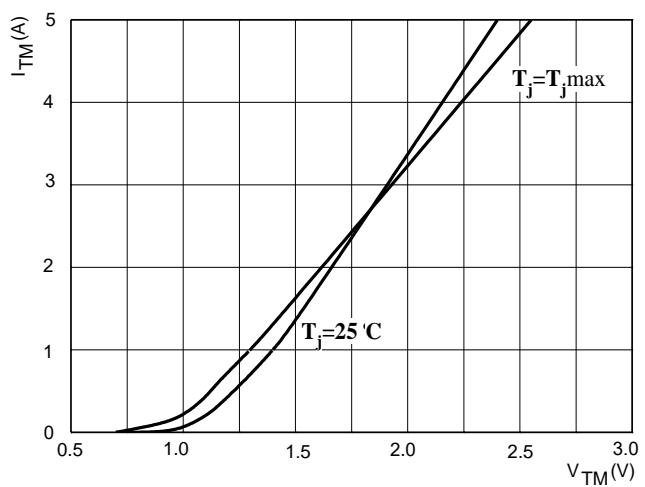


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$

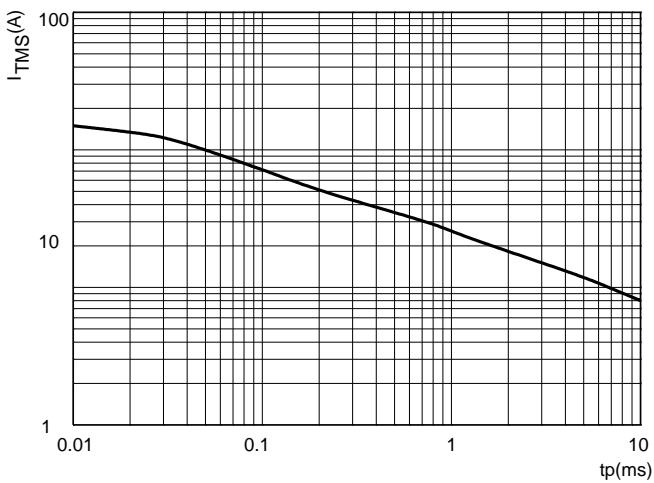
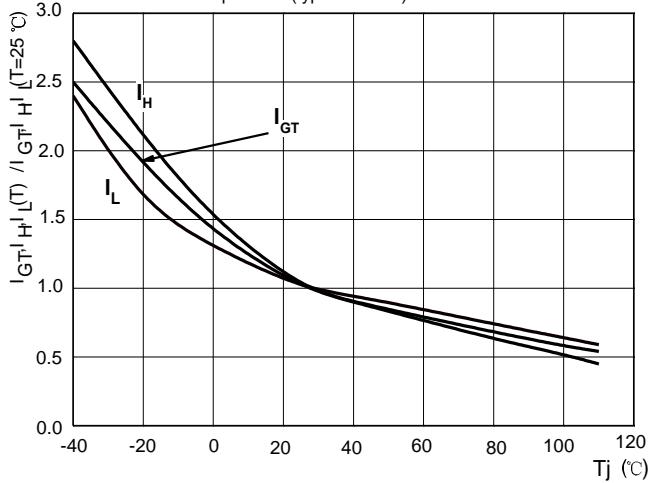
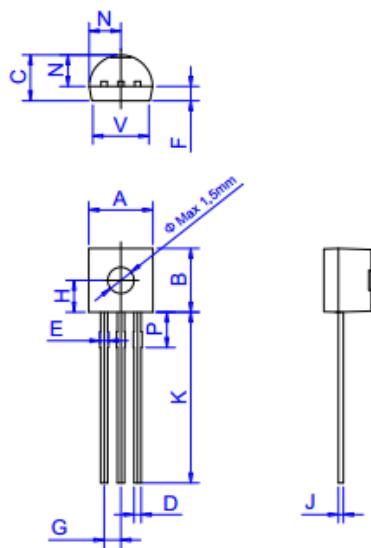


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



TO-92K PACKAGE OUTLINE DIMENSIONS



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.60		0.80	0.024		0.031
F	-	1.1	-	-	0.043	-
G	-	1.27	-	-	0.050	-
H	-	2.30	-	-	0.091	-
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.86		2.06	0.073		0.081
V	-		4.3	-		0.169

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Triacs](#) category:

Click to view products by [CJ manufacturer](#):

Other Similar products are found below :

[T2035H-6G](#) [BT137-600-0Q](#) [Z0409MF0AA2](#) [Z0109NA 2AL2](#) [ACST1635T-8FP](#) [BCR20RM-30LA#B00](#) [CMA60MT1600NHR](#) [NTE5611](#)
[NTE5612](#) [NTE5613](#) [NTE5621](#) [NTE5623](#) [NTE5629](#) [NTE5638-08](#) [NTE5688](#) [NTE5689](#) [NTE5690](#) [T1235T-8I](#) [BTA312-600CT.127](#) [T1210T-8G-TR](#) [Z0109NN0,135](#) [T2535T-8I](#) [T2535T-8T](#) [TN4050-12WL](#) [MAC4DLM-1G](#) [BT137-600E,127](#) [BT137X-600D](#) [BT148W-600R,115](#)
[BT258-500R,127](#) [BTA08-800BW3G](#) [BTA140-800,127](#) [BTA30-600CW3G](#) [BTA30-600CW3G](#) [BTB08-800BW3G](#) [BTB16-600CW3G](#)
[BTB16-600CW3G](#) [Z0410MF0AA2](#) [Z0109MN,135](#) [T825T-6I](#) [T1635T-6I](#) [T1220T-6I](#) [NTE5638](#) [TYN612MRG](#) [TYN1225RG](#) [TPDV840RG](#)
[ACST1235-8FP](#) [ACS302-6T3-TR](#) [BT134-600D,127](#) [BT134-600G,127](#) [BT136X-600E,127](#)